Jiang Yin

List of Publications by Year in descending order

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31	807	471509 17	477307 29
papers	citations	h-index	g-index

32	32	32	1389
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Crystallization, phase evolution and ferroelectric properties of solâ€“gel-synthesized Ba(Ti_{0.8}Zr_{0.2})O₃â€“x(Ba_{0.7}Ca_{0.3})TiO₃ thin films. Journal of Materials Chemistry C, 2013, 1, 522-530.	3.3	97
2	Unexpected Magnetic Semiconductor Behavior in Zigzag Phosphorene Nanoribbons Driven by Half-Filled One Dimensional Band. Scientific Reports, 2015, 5, 8921.	3.3	88
3	The effect of thermal treatment induced inter-diffusion at the interfaces on the charge trapping performance of HfO2/Al2O3 nanolaminate-based memory devices. Journal of Applied Physics, 2013, 114, .	2.5	54
4	Upward ferroelectric self-polarization induced by compressive epitaxial strain in (001) BaTiO3 films. Journal of Applied Physics, 2013, 113, .	2.5	48
5	The interface inter-diffusion induced enhancement of the charge-trapping capability in HfO2/Al2O3 multilayered memory devices. Applied Physics Letters, 2013, 103, .	3.3	44
6	Memristive behaviors of LiNbO3 ferroelectric diodes. Applied Physics Letters, 2010, 97, 012902.	3.3	40
7	The development of BiFeO3-based ceramics. Science Bulletin, 2014, 59, 5161-5169.	1.7	40
8	Ga 2 Te 3 phase change material for low-power phase change memory application. Applied Physics Letters, 2010, 97, .	3.3	39
9	Conduction behavior change responsible for the resistive switching as investigated by complex impedance spectroscopy. Applied Physics Letters, 2007, 91, .	3.3	38
10	A TiAl2O5 nanocrystal charge trap memory device. Applied Physics Letters, 2010, 97, 143504.	3.3	37
11	Strain tunable magnetism in SnX2 (Xâ€‰=â€‰S, Se) monolayers by hole doping. Scientific Reports, 2016, 6, 39218.	3.3	36
12	Quantum spin Hall insulator phase in monolayer WTe2 by uniaxial strain. AIP Advances, 2016, 6, .	1.3	31
13	Carrier-tunable magnetism in two dimensional graphene-like C₂N. RSC Advances, 2016, 6, 54027-54031.	3.6	28
14	Memristive learning and memory functions in polyvinyl alcohol polymer memristors. AIP Advances, 2014, 4, .	1.3	20
15	Synthesis of PbI₂ nanowires for high sensitivity photodetectors. RSC Advances, 2016, 6, 59445-59449.	3.6	20
16	Tunable electronic structures in MPX₃ (M = Zn, Cd; X = S, Se) monolayers by strain engineering. RSC Advances, 2016, 6, 89901-89906.	3.6	19
17	Structural Evolving Sequence and Porous <scp><scp>Ba</scp></scp>₆<scp><scp>Zr</scp></scp>₂<scp><scp>Nb</scp></scp>₈<scp>< Ferroelectric Ceramics with Ultrahigh Breakdown Field and Zero Strain. Journal of the American Ceramic Society, 2013, 96, 555-560.	3.8	17
18	The magnetism of 1T-MX₂ (M = Zr, Hf; X = S, Se) monolayers by hole doping. RSC Advances, 2019, 9, 13561-13566.	3.6	16

#	Article	IF	Citations
19	Enhanced memory performance by tailoring the microstructural evolution of (ZrO2)0.6(SiO2)0.4 charge trapping layer in the nanocrystallites-based charge trap flash memory cells. Applied Physics A: Materials Science and Processing, 2012, 108, 217-222.	2.3	15
20	Enhanced Performance of Organic Fieldâ€Effect Transistor Memory by Holeâ€Barrier Modulation with an Nâ€Type Organic Buffer Layer between Pentacene and Polymer Electret. Advanced Electronic Materials, 2020, 6, 1901184.	5.1	14
21	Preparation and characterization of GeTe4 thin films as a candidate for phase change memory applications. Journal of Applied Physics, 2011, 109, .	2.5	13
22	Enhancement of Memory Properties of Pentacene Field-Effect Transistor by the Reconstruction of an Inner Vertical Electric Field with an n-Type Semiconductor Interlayer. ACS Applied Materials & Interfaces, 2021, 13, 13452-13458.	8.0	12
23	Highâ€Performance Pentaceneâ€Based Fieldâ€Effect Transistor Memory Using the Electrets of Polymer Blends. Advanced Electronic Materials, 2022, 8, .	5.1	10
24	Encoding, training and retrieval in ferroelectric tunnel junctions. Scientific Reports, 2016, 6, 27022.	3.3	8
25	Continuously-tuned tunneling behaviors of ferroelectric tunnel junctions based on BaTiO3/La0.67Sr0.33MnO3 heterostructure. AIP Advances, 2014, 4, .	1.3	7
26	Electronâ€beam induced phase transformation in Î²â€Ag₂Se thin films. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 135-138.	1.8	6
27	The roles of the dielectric constant and the relative level of conduction band of high-k composite with Si in improving the memory performance of charge-trapping memory devices. AIP Advances, 2014, 4, 117110.	1.3	4
28	Redox-controlled memristive switching in the junctions employing Ti reactive electrodes. AIP Advances, 2011, 1, 032141.	1.3	3
29	Enhanced leakage current properties of HfO2/GaN gate dielectric stack by introducing an ultrathin buffer layer. Journal of Materials Science: Materials in Electronics, 2014, 25, 152-156.	2.2	3
30	Enhanced half-metallicity in the zigzag graphene nanoribbons by adsorption of the zigzag hydrogen fluoride molecular chains. AIP Advances, 2014, 4, 067132.	1.3	0
31	Piezoelectricity in two-dimensional covalent organic frameworks. Journal of Applied Physics, 2017, 121, 225112.	2.5	0